The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-23. (Canceled)

24. (Currently Amended) A method for manufacturing a thin film transistor comprising:

forming a crystalline semiconductor film by irradiating with an energy beam output continuously while scanning the energy beam;

forming a gate electrode over the crystalline semiconductor film; and

forming an impurity region in the crystalline semiconductor film using the gate electrode as a mask,

wherein the energy beam is blocked in a position in which a scanning direction of the energy beam changes.

25. (Currently Amended) A method for manufacturing a thin film transistor comprising:

forming a crystalline semiconductor film by irradiating with an energy beam output continuously while scanning the energy beam;

forming a gate electrode over the crystalline semiconductor film; and

forming an impurity region in the crystalline semiconductor film using the gate electrode as a mask,

wherein the energy beam is blocked in a position where a scanning of the energy beam starts and in a position where the scanning thereof ends.

26. (Previously Presented) A method for manufacturing a thin film transistor according to claim 24 or 25, wherein the energy beam is scanned by using a galvanometer mirror or a polygon mirror.

27. (Currently Amended) A method for manufacturing a thin film transistor comprising:

forming a crystalline semiconductor film by using a beam irradiation apparatus, the beam irradiation apparatus comprising means for scanning an energy beam output continuously from one end to the other end, and means for blocking the energy beam in the one end and in the other end[[,]];

forming a gate electrode over the crystalline semiconductor film; and

forming an impurity region in the crystalline semiconductor film by using the gate electrode as a mask.

28. (Previously Presented) A method for manufacturing a thin film transistor comprising:

forming a crystalline semiconductor film by using a beam irradiation apparatus, the beam irradiation apparatus comprising means for scanning an energy beam output continuously from one end to the other end, and means for blocking the energy beam in the one end and in the other end in synchronization with the means for scanning;

forming a gate electrode over the crystalline semiconductor film; and

forming an impurity region in the crystalline semiconductor film by using the gate electrode as a mask.

29. (Previously Presented) A method for manufacturing a thin film transistor comprising:

forming a crystalline semiconductor film by using a beam irradiation apparatus, the beam irradiation apparatus comprising a plurality of means for scanning a plurality

of energy beams output continuously from one end to the other end, and a plurality of means for blocking the energy beams in the one end and in the other end;

forming a gate electrode over the crystalline semiconductor film; and

forming an impurity region in the crystalline semiconductor film by using the gate electrode as a mask.

30. (Currently Amended) A method for manufacturing a thin film transistor comprising:

forming a crystalline semiconductor film by using a beam irradiation apparatus, the beam irradiating apparatus comprising means for scanning an energy beam output continuously from one end to the other end, and means for blocking the energy beam in the one end and in the other end, wherein the means for scanning has a specular body having a plane surface or a curved surface, wherein the specular body is fixed to a shaft so as to be arranged on an optical axis of the energy beam, and wherein the specular body vibrates by using the shaft as its center[[,]];

forming a gate electrode over the crystalline semiconductor film; and

forming an impurity region in the crystalline semiconductor film using the gate electrode as a mask.

31. (Previously Presented) A method for manufacturing a thin film transistor comprising:

forming a crystalline semiconductor film by using a beam irradiation apparatus, the beam irradiating apparatus comprising means for scanning an energy beam output continuously from one end to the other end, and means for blocking the energy beam in the one end and in the other end, wherein the means for scanning has a specular body having a plane surface or a curved surface, wherein the specular body is fixed to a shaft so as to be arranged on an optical axis of the energy beam, and wherein the specular body rotates by using the shaft as its center;

forming a gate electrode over the crystalline semiconductor film; and

forming an impurity region in the crystalline semiconductor film using the gate electrode as a mask.

32. (Original) A method for manufacturing a thin film transistor according to any one of claims 27 to 31, wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO4 laser, a YAG laser, a YLF laser, a $YAlO_3$ laser and an Ar laser.

33. (Previously Presented) A method for manufacturing a thin film transistor according to any one of claims 24, 25 and 27 to 31, wherein the thin film transistor is incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, a mobile phone, and an electronic book reader.

34. (Previously Presented) A method for manufacturing a thin film transistor according to claim 27, wherein a light-blocking plate or a chopper is used as the means for blocking the energy beam.

35. (Previously Presented) A method for manufacturing a thin film transistor according to claim 28, wherein a light-blocking plate or a chopper is used as the means for blocking the energy beam.

36. (Previously Presented) A method for manufacturing a thin film transistor according to claim 29, wherein a light-blocking plate or a chopper is used as the means for blocking the energy beam.

37. (Previously Presented) A method for manufacturing a thin film transistor according to claim 30, wherein a light-blocking plate or a chopper is used as the means for blocking the energy beam.

38. (Previously Presented) A method for manufacturing a thin film transistor according to claim 31, wherein a light-blocking plate or a chopper is used as the means for blocking the energy beam.

39. (New) A method for manufacturing a thin film transistor according to claim 27, wherein a galvanometer mirror is used as the means for scanning the energy beam.

40. (New) A method for manufacturing a thin film transistor according to claim 28, wherein a galvanometer mirror is used as the means for scanning the energy beam.

41. (New) A method for manufacturing a thin film transistor according to claim 29, wherein a galvanometer mirror is used as the means for scanning the energy beam.

42. (New) A method for manufacturing a thin film transistor according to claim 30, wherein a galvanometer mirror is used as the means for scanning the energy beam.

43. (New) A method for manufacturing a thin film transistor according to claim 31, wherein a galvanometer mirror is used as the means for scanning the energy beam.